D1 C1 while leaving said conductive structure substantially unoxidized by introducing O_2 and H_2 in an explosive reaction to said insulating layer, said silicon-containing structure and said conductive structure, such that the reaction between said O_2 and H_2 does not increase the pressure in the processing chamber beyond a predetermined level.

Sub D2 C2 9 (Thrice Amended). A method of oxidizing, in a semiconductor processing chamber, a first feature while leaving a second feature substantially unoxidized, said method comprised of subjecting said first and second features to O_2 and H_2 in an explosive reaction, such that the reaction between said O_2 and H_2 does not increase the pressure in the processing chamber beyond a predetermined level.

Sub D3 16 (Thrice Amended). A method of fabricating, in a semiconductor processing chamber, a capacitor having a dielectric between a bottom electrode and a top electrode and situated over a semiconductor substrate, said method comprising the steps of:

providing said bottom electrode over said semiconductor substrate;

C3 providing a dielectric material over said bottom electrode; and

subjecting said bottom electrode and said dielectric material to O_2 and H_2 in an explosive reaction, wherein said dielectric material is oxidized and said bottom electrode remains substantially unoxidized, such that the reaction between said O_2 and H_2 does not increase the pressure in the processing chamber beyond a predetermined level.

C4 20 (Twice Amended). The method of claim 1 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing O_2 and H_2 in an explosive reaction in a portion of a process chamber's total volume, such that reaction between the O_2 and H_2 occurs continuously as the O_2 and H_2 enter the chamber.

22 (Twice Amended). The method of claim 9 and further comprising the step of introducing O_2 and H_2 in an explosive reaction in a portion of a process chamber's total volume, such that reaction between the O_2 and H_2 occurs continuously as the O_2 and H_2 enter the chamber.

24 (Twice Amended). The method of claim 16 and further comprising the step of introducing O_2 and H_2 in an explosive reaction in a portion of a process chamber's total volume, such that reaction between the O_2 and H_2 occurs continuously as the O_2 and H_2 enter the chamber.

26 (Twice Amended). A method of fabricating an electrical device formed in a semiconductor substrate, said method comprising:

forming an insulating layer over said semiconductor substrate;

forming a silicon-containing structure on said insulating layer;

forming a conductive structure on said silicon-containing structure; and

oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing an oxygen-containing gas selected from the group consisting of O_2, N_2O, NO or CO_2 and a separate hydrogen-containing gas to said insulating layer, said silicon-containing structure and said conductive structure, such that an explosive reaction between said the hydrogen-containing gas and the oxygen containing gas does not increase the pressure in the processing chamber beyond a predetermined level.

27 (Twice Amended). The method of claim 26 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing said oxygen-containing gas and said hydrogen containing gas in a portion of a process chamber's total volume, such that an explosive reaction between the the hydrogen-containing gas and the oxygen containing gas occurs continuously as the the hydrogen-containing gas and the oxygen containing gas enter the chamber.

29 (Amended). The method of claim 1 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing O_2 and H_2 while the chamber is at a low pressure and increasing the pressure once the reaction begins.

30 (Amended). The method of claim 9 and further comprising the step of introducing O_2 and H_2 while the chamber is at a low pressure and increasing the pressure once the reaction begins.

31 (Amended). The method of claim 16 and further comprising the step of introducing O_2 and H_2 while the chamber is at a low pressure and increasing the pressure once the reaction begins.

32 (Amended). The method of claim 26 wherein said oxidizing step comprises the step of oxidizing a portion of said insulating layer and said silicon-containing structure while leaving said conductive structure substantially unoxidized by introducing said oxygen-containing gas and said hydrogen containing gas while the chamber is at a low pressure and increasing the pressure once the reaction begins.